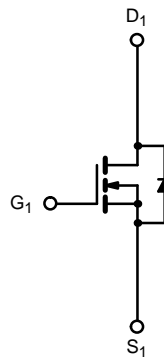
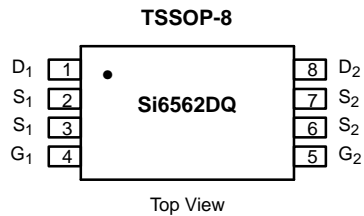


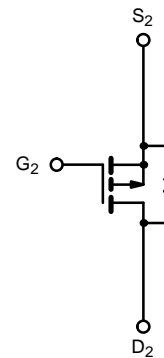
N- and P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.030 @ $V_{GS} = 4.5$ V	± 4.5
		0.040 @ $V_{GS} = 2.5$ V	± 3.9
P-Channel	-20	0.050 @ $V_{GS} = -4.5$ V	± 3.5
		0.085 @ $V_{GS} = -2.5$ V	± 2.7

TrenchFET[®]
Power MOSFETs
2.5-V Rated



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 12	± 12	V
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	± 4.5	A
		$T_A = 70^\circ\text{C}$	± 3.6	
Pulsed Drain Current	I_{DM}	± 30	± 30	A
Continuous Source Current (Diode Conduction) ^a	I_S	1.25	-1.25	A
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	1.0	W
		$T_A = 70^\circ\text{C}$	0.64	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P-Channel	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	125	$^\circ\text{C}/\text{W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.



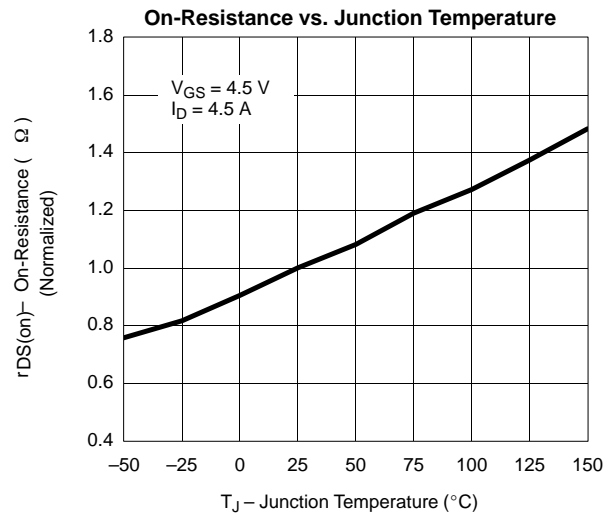
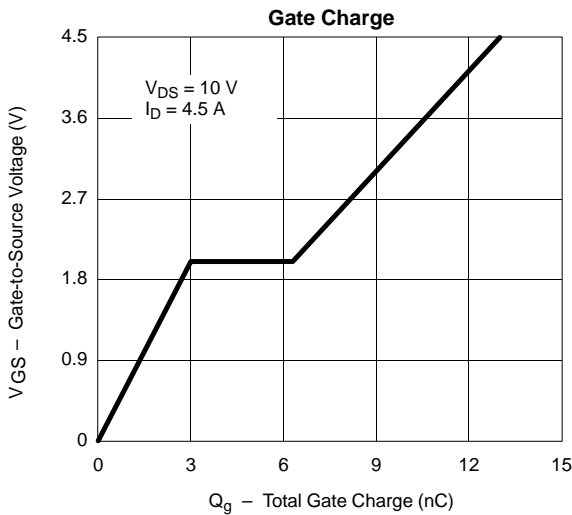
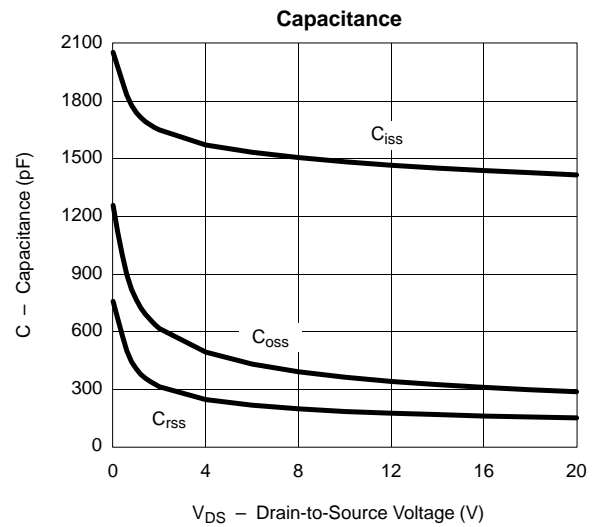
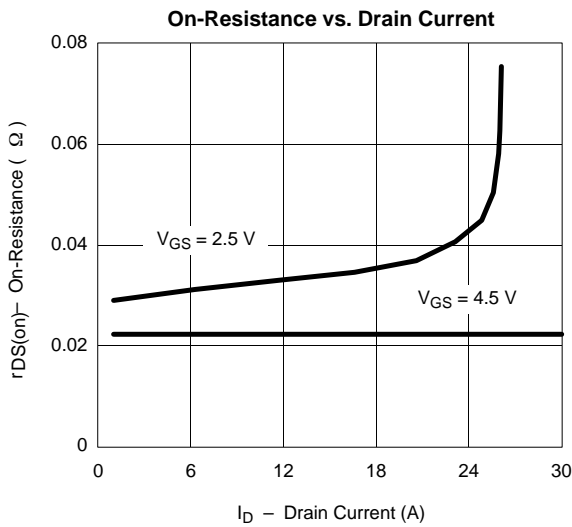
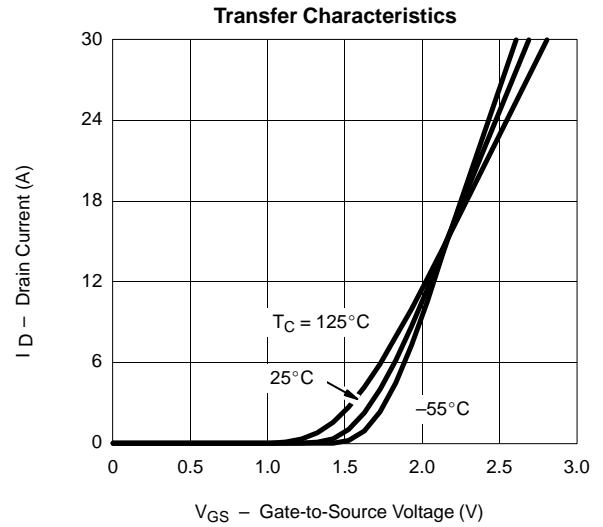
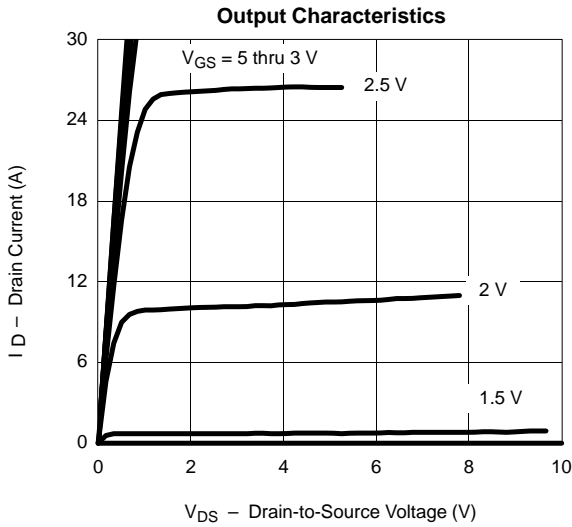
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.6			V
		V _{DS} = V _{GS} , I _D = -250 μA	P-Ch	-0.6			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V	N-Ch			±100	nA
			P-Ch			±100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = -20 V, V _{GS} = 0 V	P-Ch			-1	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			25	
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			-25	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	30			A
		V _{DS} ≥ -5 V, V _{GS} = -4.5 V	P-Ch	-30			
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 4.5 A	N-Ch		0.023	0.030	Ω
		V _{GS} = -4.5 V, I _D = -3.5 A	P-Ch		0.040	0.050	
		V _{GS} = 2.5 V, I _D = 3.9 A	N-Ch		0.030	0.040	
		V _{GS} = -2.5 V, I _D = -2.7 A	P-Ch		0.060	0.085	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 4.5 A	N-Ch		20		S
		V _{DS} = -10 V, I _D = -3.5 A	P-Ch		10		
Diode Forward Voltage ^a	V _{SD}	I _S = 1.25 A, V _{GS} = 0 V	N-Ch		0.65	1.2	V
		I _S = -1.25 A, V _{GS} = 0 V	P-Ch		0.72	-1.2	
Dynamic^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 4.5 A P-Channel V _{DS} = -15 V, V _{GS} = -4.5 V, I _D = -3.5 A	N-Ch		13	25	nC
			P-Ch		14.5	25	
Gate-Source Charge	Q _{gs}		N-Ch		3.0		
			P-Ch		3.5		
Gate-Drain Charge	Q _{gd}		N-Ch		3.3		
			P-Ch		3.5		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 10 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω P-Channel V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -10 V, R _G = 6 Ω	N-Ch		22	50	ns
			P-Ch		27	50	
Rise Time	t _r		N-Ch		40	80	
			P-Ch		30	60	
Turn-Off Delay Time	t _{d(off)}		N-Ch		50	100	
			P-Ch		57	100	
Fall Time	t _f		N-Ch		20	40	
			P-Ch		21	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.25 A, di/dt = 100 A/μs	N-Ch		30	60	
		I _F = -1.25 A, di/dt = 100 A/μs	P-Ch		60	100	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

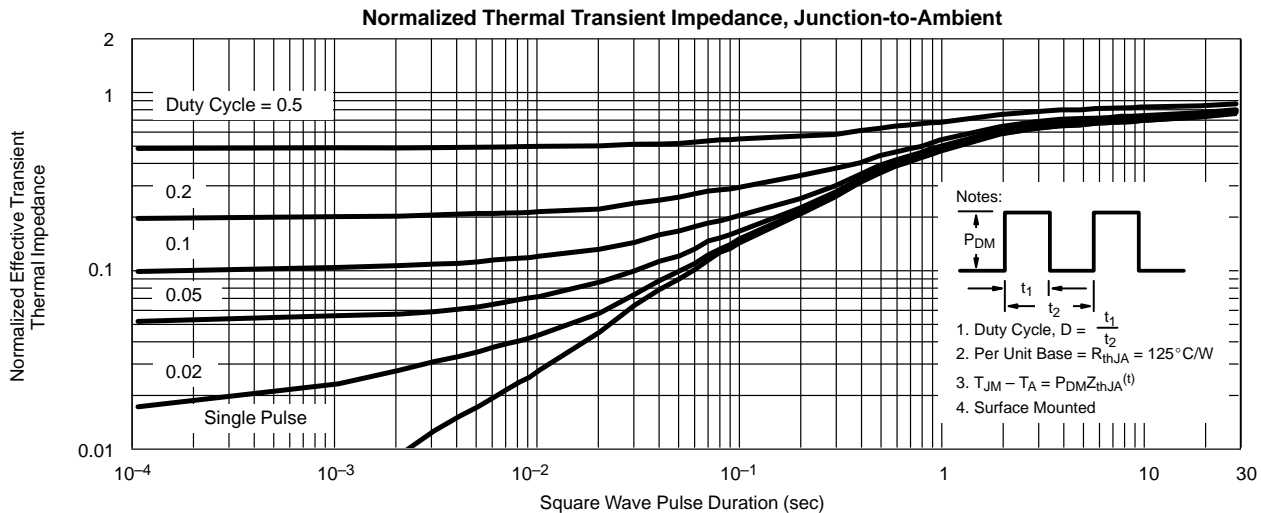
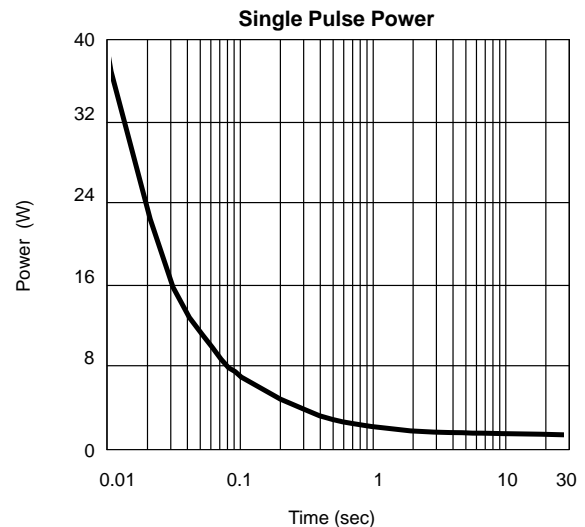
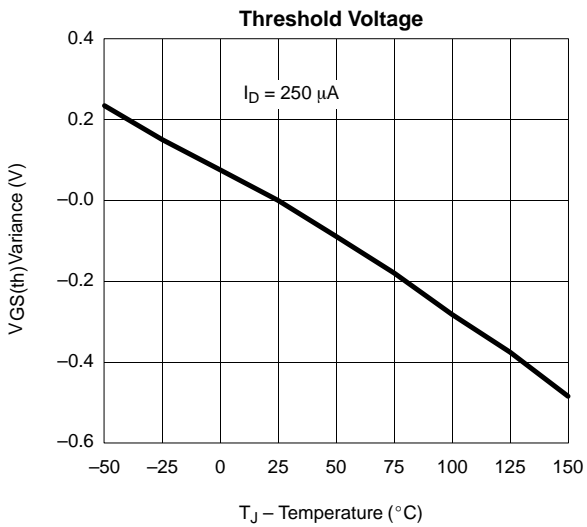
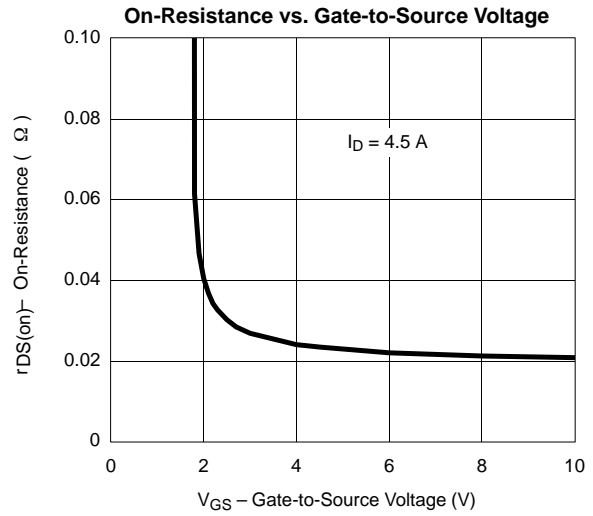
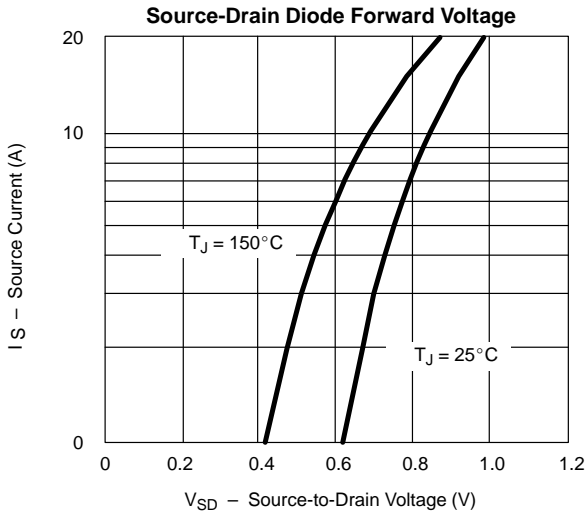


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

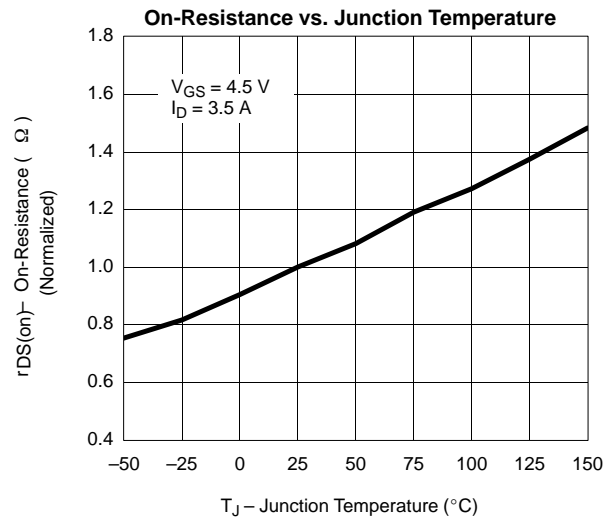
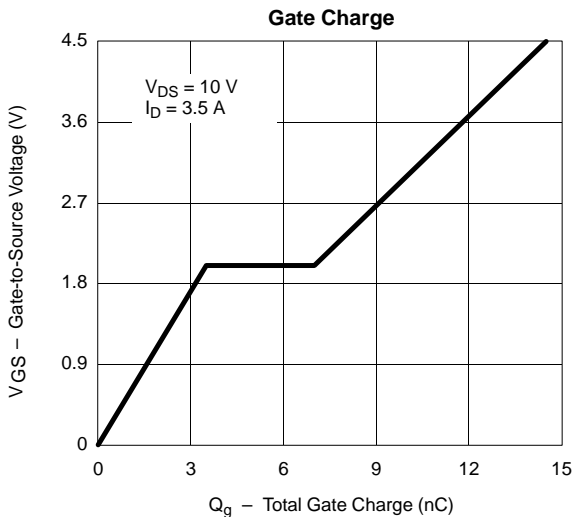
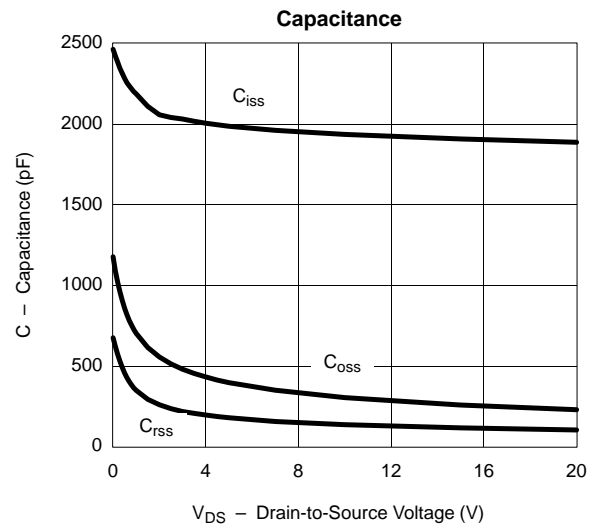
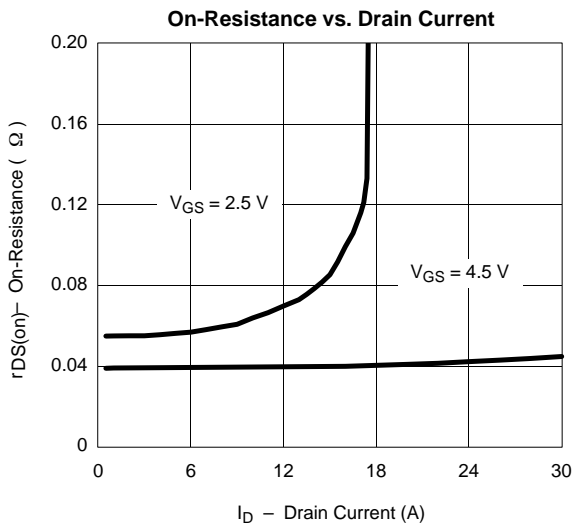
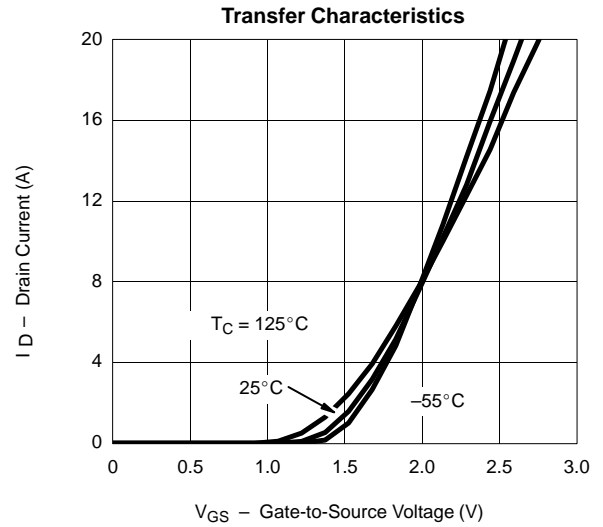
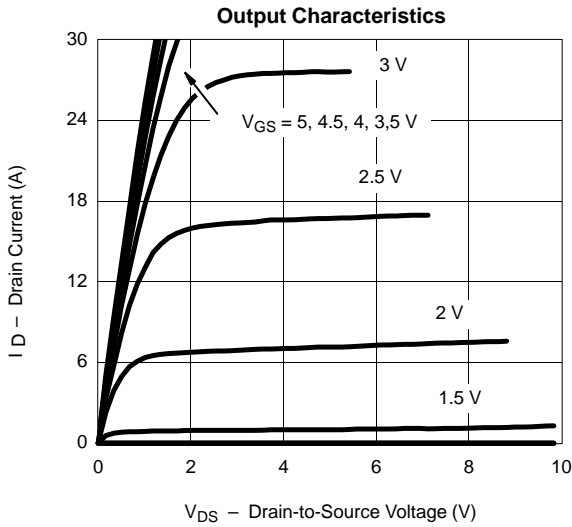




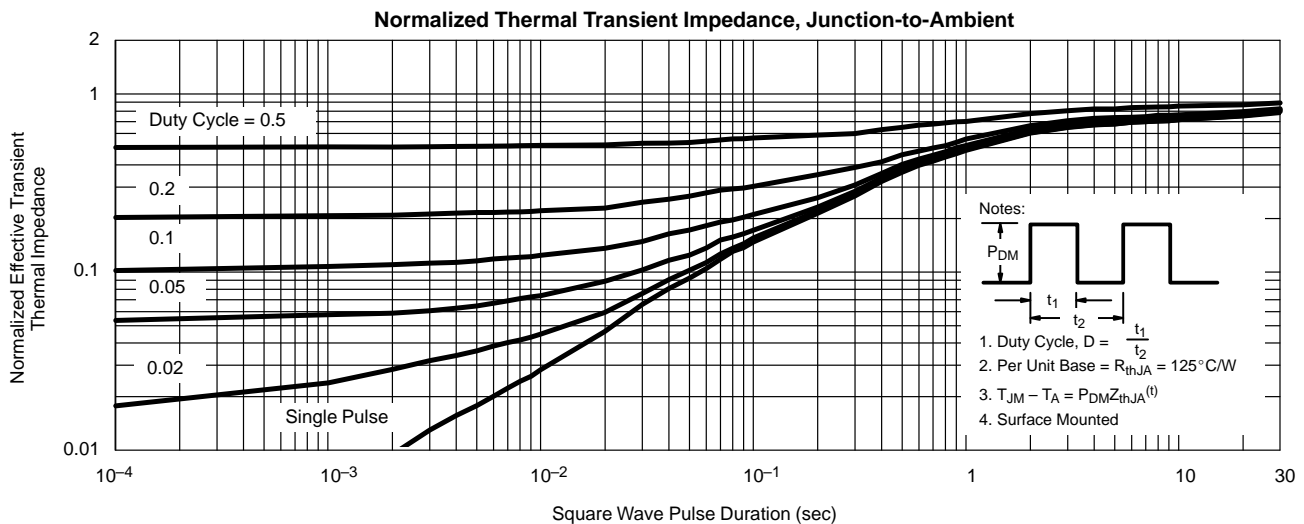
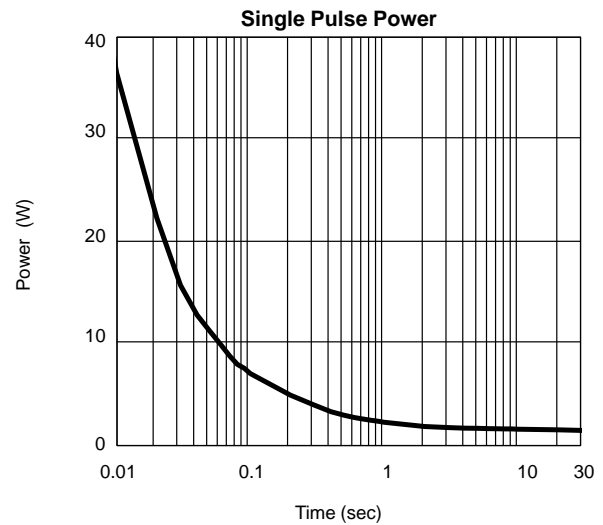
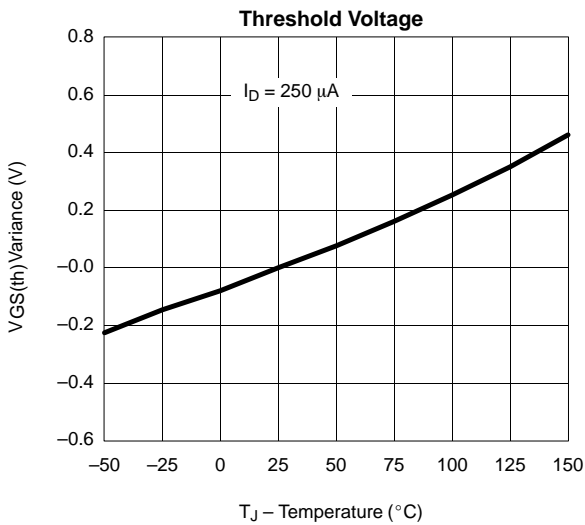
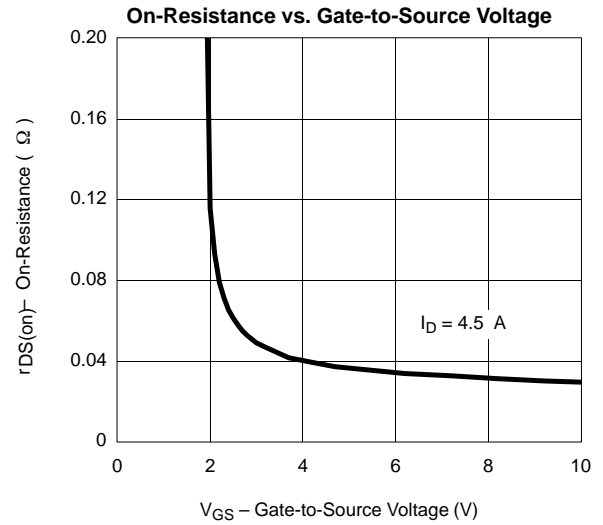
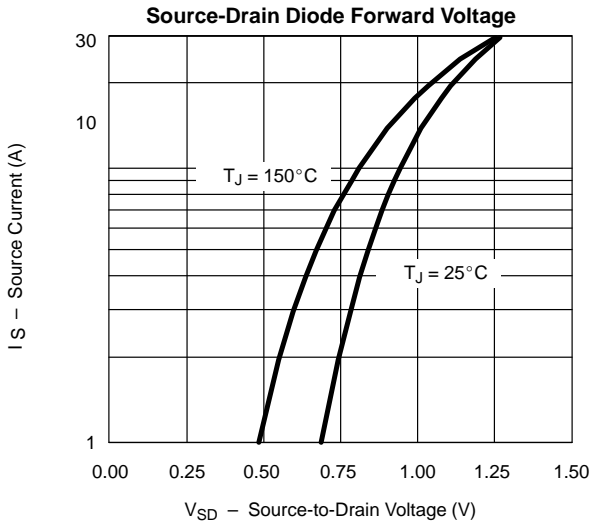
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL





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